

Switch-mode Schottky Power Rectifier

250 V, 40 A

MBR40250G, MBR40250TG, MBRF40250TG, MBRB40250TG

Features

- 250 V Blocking Voltage
- Low Forward Voltage Drop, $V_F = 0.86 \text{ V}$
- Soft Recovery Characteristic, T_{RR} < 35 ns
- Stable Switching Performance Over Temperature
- These Devices are Pb-Free and are RoHS Compliant

Benefits

- Reduces or Eliminates Reverse Recovery Oscillations
- Minimizes Need for EMI Filtering
- Reduces Switching Losses
- Improved Efficiency

Applications

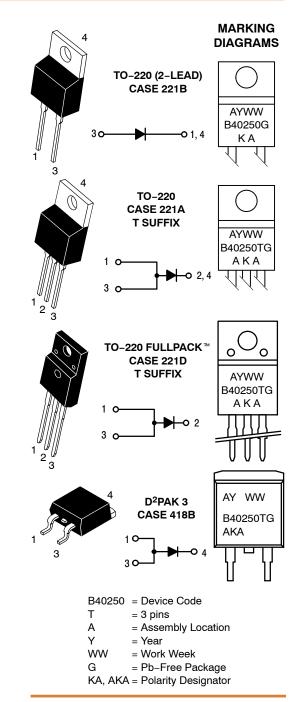
- Power Supply
- · Power Management
- Automotive
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable

1

- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Epoxy Meets UL 94 V-0 at 0.125 in



ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

MBR40250G, MBR40250TG, MBRF40250TG, MBRB40250TG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	250	V
Average Rectified Forward Current (Rated V_R) T_C = 82°C MBR40250, MBR40250T, MBRB40250T (Rated V_R) T_C = 46°C MBRF40250T	I _{F(AV)}	40	А
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz) T_C = 82°C MBR40250, MBR40250T, MBRB40250T (Rated V_R , Square Wave, 20 kHz) T_C = 46°C MBRF40250T	I _{FRM}	80	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150	А
Storage Temperature	T _{stg}	-65 to +175	°C
Operating Junction Temperature	T_J	-65 to +150	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance			°C/W
Junction-to-Case	$R_{ heta JC}$		
MBR40250(T) and MBRB40250T	****	2.0	
MBRF40250		3.0	
Junction-to-Ambient	$R_{ heta JA}$		
MBR40250(T)		60	
MBRF40250		50	
MBRB40250T		50	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 1) I_F = 20 A, T_C = 25°C I_F = 20 A, T_C = 125°C I_F = 40 A, T_C = 25°C I_F = 40 A, T_C = 125°C	V _F	0.86 0.71 0.97 0.86	V
Maximum Instantaneous Reverse Current (Note 1) Rated DC Voltage, $T_C = 25^{\circ}C$ Rated DC Voltage, $T_C = 125^{\circ}C$	I _R	0.25 30	mA
Maximum Reverse Recovery Time $I_F = 1.0$ A, di/dt = 50 A/ μ s, $T_C = 25^{\circ}C$	t _{rr}	35	ns

DYNAMIC CHARACTERISTICS

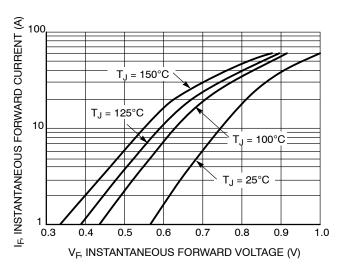
Capacitance V _B = -5.0 V, T _C = 25°C, Frequency = 1.0 MHz	C _T	500	pF
$V_R = -5.0 \text{ V}$, $I_C = 25^{\circ}\text{C}$, Frequency = 1.0 MHz		500	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2.0%.

MBR40250G, MBR40250TG, MBRF40250TG, MBRB40250TG

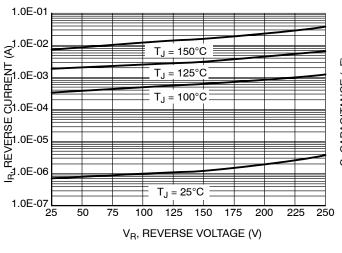
TYPICAL CHARACTERISTICS



 $\begin{array}{c} \text{ (V)} \\ \text{ WINDWYM} \\ \text{ IO} \\ \text{ T}_{\text{J}} = 150^{\circ}\text{C} \\ \text{ T}_{\text{J}} = 125^{\circ}\text{C} \\ \text{ T}_{\text{J}} = 25^{\circ}\text{C} \\ \text{ T}_{\text{J}} = 25^{\circ}\text{C} \\ \text{ V}_{\text{F}}, \text{ MAXIMUM FORWARD VOLTAGE (V)} \\ \end{array}$

Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage



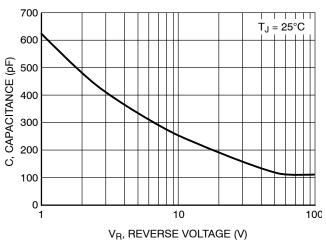
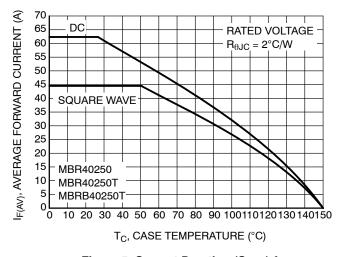


Figure 3. Typical Reverse Current

Figure 4. Typical Capacitance



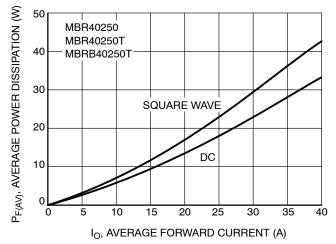
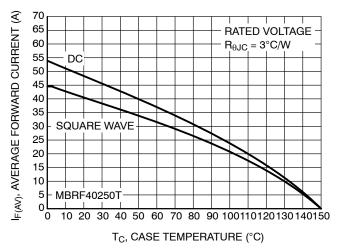


Figure 5. Current Derating (Case) for MBR40250, MBR40250T and MBRB40250T

Figure 6. Forward Power Dissipation for MBR40250, MBR40250T and MBRB40250T

MBR40250G, MBR40250TG, MBRF40250TG, MBRB40250TG

TYPICAL CHARACTERISTICS



P_{F(AV)}, AVERAGE POWER DISSIPATION (W) 50 MBRF40250T 40 30 SQUARE WAVE 20 DC 10 15 20 25 35 30 40 I_{O} , AVERAGE FORWARD CURRENT (A)

Figure 7. Current Derating (Case) for MBRF40250T

Figure 8. Forward Power Dissipation for MBRF40250T

ORDERING INFORMATION

Device	Package	Shipping [†]
MBR40250G	TO-220 (2-LEAD) (Pb-Free)	50 Units / Rail
MBR40250TG	TO-220 (Pb-Free)	50 Units / Rail
MBRF40250TG	TO-220 FULLPACK (Pb-Free)	50 Units / Rail
MBRB40250TG	D ² PAK 3 (Pb-Free)	50 Units / Rail
MBRB40250TT4G	D ² PAK 3 (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

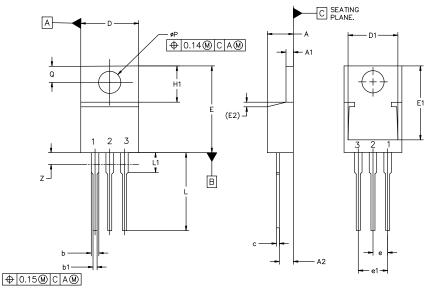
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TO-220-3 10.10x15.12x4.45, 2.54P CASE 221A **ISSUE AL**

DATE 05 FEB 2025



MILLIMETERS					
DIM	MIN	NOM	MAX		
Α	4.07	4.45	4.83		
A1	1.15	1.28	1.41		
A2	2.04	2.42	2.79		
Ь	1.15	1.34	1.52		
b1	0.64	0.80	0.96		
C	0.36	0.49	0.61		
D	9.66	10.10	10.53		
D1	8.43	8.63	8.83		
E	14.48	15.12	15.75		
E1	12.58	12.78	12.98		
E2	E2 1.27 REF				

MILLIMETERS					
DIM	MIN	NOM	MAX		
е	2.42	2.54	2.66		
e1	4.83	5.08	5.33		
H1	5.97	6.22	6.47		
L	12.70	13.49	14.27		
L1	2.80	3.45	4.10		
Q	2.54	2.79	3.04		
ØΡ	3.60	3.85	4.09		
Z		-,	3.48		

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12:	
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

Q

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

STYLE 2: PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

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SCALE 1:1

3. CATHODE

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

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AYWW

xxxxxxG

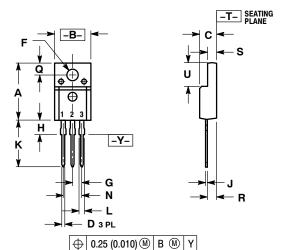
AKA

Rectifier

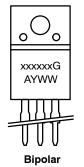
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100	BSC	2.54	BSC
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200	BSC	5.08	BSC
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

MARKING DIAGRAMS



STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER CATHODE
 ANODE 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE



= Assembly Location xxxxxx = Specific Device Code G = Pb-Free Package Υ = Year Α = Assembly Location WW = Work Week Υ = Year XXXXXX = Device Code = Work Week = Pb-Free Package WW G AKA = Polarity Designator

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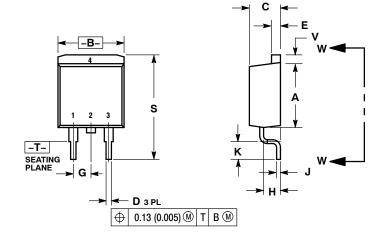




D²PAK 3 CASE 418B-04 **ISSUE L**

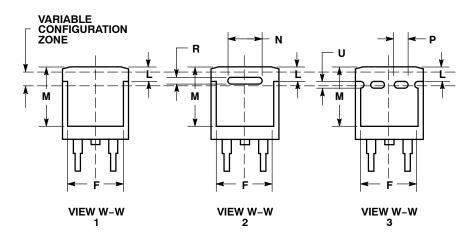
DATE 17 FEB 2015

SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6:

PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

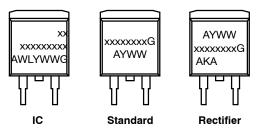
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DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*

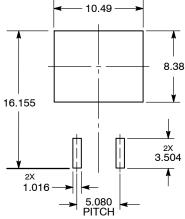


xx = Specific Device Code A = Assembly Location

WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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